Triple buffer gate Rev. 6 — 11 December 2013

1. **General description**

The 74HC3G34; 74HCT3G34 is a triple buffer. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC}.

Features and benefits 2.

- Wide supply voltage range from 2.0 V to 6.0 V
- Input levels:
 - For 74HC3G34: CMOS level
 - For 74HCT3G34: TTL level
- Complies with JEDEC standard no. 7 A
- Symmetrical output impedance
- High noise immunity
- Low-power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
 - HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Specified from -40 °C to +85 °C and -40 °C to +125 °C

Ordering information 3.

Table 1. **Ordering information**

Type number	Package				
	Temperature range	Name	Description	Version	
74HC3G34DP	–40 °C to +125 °C	TSSOP8			
74HCT3G34DP			body width 3 mm; lead length 0.5 mm		
74HC3G34DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads;	SOT765-1	
74HCT3G34DC			body width 2.3 mm		
74HC3G34GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads;	SOT996-2	
74HCT3G34GD			8 terminals; body $3 \times 2 \times 0.5$ mm		

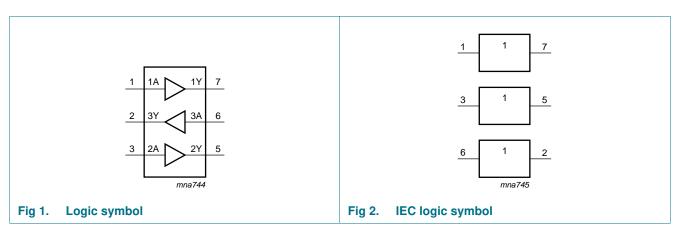


4. Marking

Table 2. Marking	
Type number	Marking code ^[1]
74HC3G34DP	H34
74HCT3G34DP	T34
74HC3G34DC	P34
74HCT3G34DC	U34
74HC3G34GD	P34
74HCT3G34GD	U34

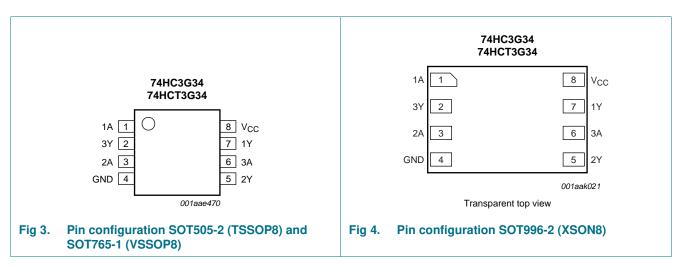
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3.	Pin description	
Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
1Y, 2Y, 3Y	7, 5, 2	data output
GND	4	ground (0 V)
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table [1]	
Input	Output
nA	nY
L	L
Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+7.0	V
I _{IK}	input clamping current	$V_{\rm I} < -0.5$ V or $V_{\rm I} > V_{\rm CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
I _{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC}$ + 0.5 V	<u>[1]</u> -	±20	mA
lo	output current	$V_{\rm O}$ = -0.5 V to (V_{\rm CC} + 0.5 V)	-	±25	mA
I _{CC}	quiescent supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K. For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K. For XSON8 package: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter Conditions		74HC3G34		74HCT3G34			Unit	
			Min	Тур	Max	Min	Тур	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
VI	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
Vo	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t / \Delta V$	input transition rise	$V_{CC} = 2.0 V$	-	-	625	-	-	-	ns/V
	and fall rate	$V_{CC} = 4.5 V$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0 V$	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7.Static characteristics

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	5 °C	–40 °C t	o +125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
74HC3G3	4							
V _{IH}	HIGH-level input	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
	voltage	$V_{CC} = 4.5 V$	3.15	2.4	-	3.15	-	V
		$V_{CC} = 6.0 V$	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 2.0 V$	-	0.8	0.5	-	0.5	V
		$V_{CC} = 4.5 V$	-	2.1	1.35	-	1.35	V
		$V_{CC} = 6.0 V$	-	2.8	1.8	-	1.8	V
V _{OH} HIGH-level output		$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu\text{A}; \ V_{CC} = 2.0 \ \text{V}$	1.9	2.0	-	1.9	-	V
		I_O = –20 $\mu A;V_{CC}$ = 4.5 V	4.4	4.5	-	4.4	-	V
		$I_{O} = -20 \ \mu A; \ V_{CC} = 6.0 \ V$	5.9	6.0	-	5.9	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
		$I_{O} = -5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	5.63	5.81	-	5.2	-	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = 20 \ \mu\text{A}; \ V_{CC} = 2.0 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; \ V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		$I_{O} = 20 \ \mu A; V_{CC} = 6.0 \ V$	-	0	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		$I_{O} = 5.2 \text{ mA}; V_{CC} = 6.0 \text{ V}$	-	0.16	0.33	-	0.4	V
1	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	±1.0	-	±1.0	μA
СС	supply current	per input pin; V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	10	-	20	μA
Ci	input capacitance		-	1.5	-	-	-	pF

Triple buffer gate

Symbol	Parameter	Conditions	-40	°C to +8	5 °C	_40 °C t	o +125 °C	Unit
			Min	Typ <mark>[1]</mark>	Max	Min	Max	
74HCT3G	i34							
V _{IH}	HIGH-level input voltage	V_{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V_{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OH}	HIGH-level output	$V_I = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_O = -20 \ \mu A; \ V_{CC} = 4.5 \ V$	4.4	4.5	-	4.4	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 4.5 \text{ V}$	4.13	4.32	-	3.7	-	V
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	$I_{O} = 20 \ \mu A; V_{CC} = 4.5 \ V$	-	0	0.1	-	0.1	V
		I_{O} = 4.0 mA; V_{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
I	input leakage current	$V_{I} = V_{CC}$ or GND; $V_{CC} = 5.5 V$	-	-	±1.0	-	±1.0	μA
I _{CC}	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = V_{CC} \text{ or } GND; \ I_{O} = 0 \ A; \\ V_{CC} = 5.5 \ V \end{array}$	-	-	10	-	20	μA
ΔI_{CC}	additional supply current	per input; V_{CC} = 4.5 V to 5.5 V; V_{I} = V_{CC} – 2.1 V; I_{O} = 0 A	-	-	375	-	410	μA
Cl	input capacitance		-	1.5	-	-	-	pF

 Table 7.
 Static characteristics ... continued

 Voltages are referenced to GND (ground = 0 V).

[1] All typical values are measured at $T_{amb} = 25 \text{ °C}$.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

Symbol	Parameter	Conditions		-40	°C to +85	5 °C	–40 °C t	o +125 °C	Unit
				Min	Typ <mark>[1]</mark>	Max	Min	Max	
74HC3G	34								
t _{pd}	propagation delay	nA to nY; see <u>Figure 5</u>	[2]						
		$V_{CC} = 2.0 V$		-	29	95	-	125	ns
		$V_{CC} = 4.5 V$		-	9	19	-	25	ns
		$V_{CC} = 6.0 V$		-	8	16	-	20	ns
tt	transition time	nY; see <u>Figure 5</u>	<u>[3]</u>						
		$V_{CC} = 2.0 V$		-	18	95	-	125	ns
		$V_{CC} = 4.5 V$		-	6	19	-	25	ns
		$V_{CC} = 6.0 V$		-	5	16	-	20	ns
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	<u>[4]</u>	-	10	-	-	-	pF

Triple buffer gate

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C t	–40 °C to +125 °C		
				Min	Typ <mark>[1]</mark>	Max	Min	Max		
74HCT3	G34						1			
t _{pd} propagation delay		nA to nY; see Figure 5	[2]							
		$V_{CC} = 4.5 V$		-	10	23	-	29	ns	
tt	transition time	nY; V_{CC} = 4.5 V; see <u>Figure 5</u>	[3]	-	6	19	-	25	ns	
C _{PD}	power dissipation capacitance	V_{I} = GND to V_{CC} – 1.5 V	<u>[4]</u>	-	9	-	-	-	pF	

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 6.

[1] All typical values are measured at $T_{amb} = 25 \ ^{\circ}C$.

- [2] t_{pd} is the same as t_{PLH} and t_{PHL} .
- [3] t_t is the same as t_{TLH} and t_{THL} .
- [4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 - $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o) = \text{sum of outputs.}$

12. Waveforms

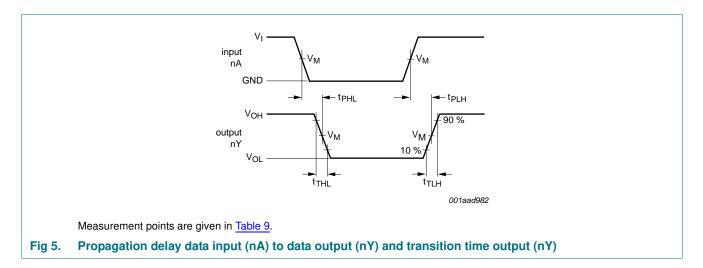


Table 9. Measurement points

Туре	Input	Output
	V _M	V _M
74HC3G34	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT3G34	1.3 V	1.3 V

74HC_HCT3G34 Product data sheet

NXP Semiconductors

74HC3G34; 74HCT3G34

Triple buffer gate

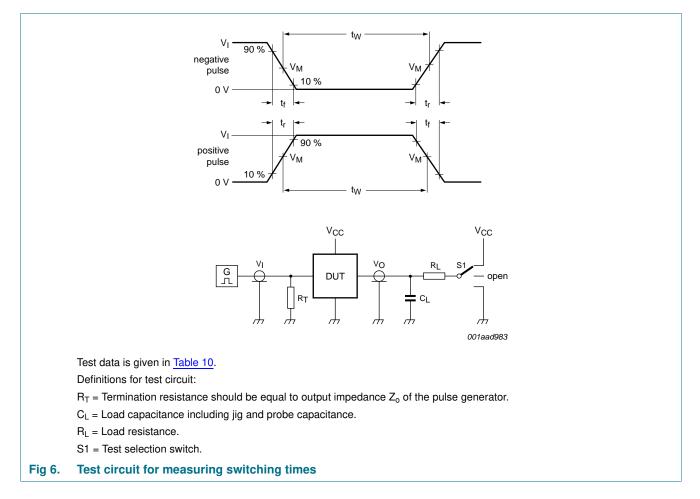


Table 10. Test data

Туре	Input		Load		S1 position
	VI	t _r , t _f	CL	RL	t _{PHL} , t _{PLH}
74HC3G34	GND to V _{CC}	≤ 6 ns	50 pF	1 kΩ	open
74HCT3G34	GND to 3 V	≤ 6 ns	50 pF	1 kΩ	open

Triple buffer gate

13. Package outline

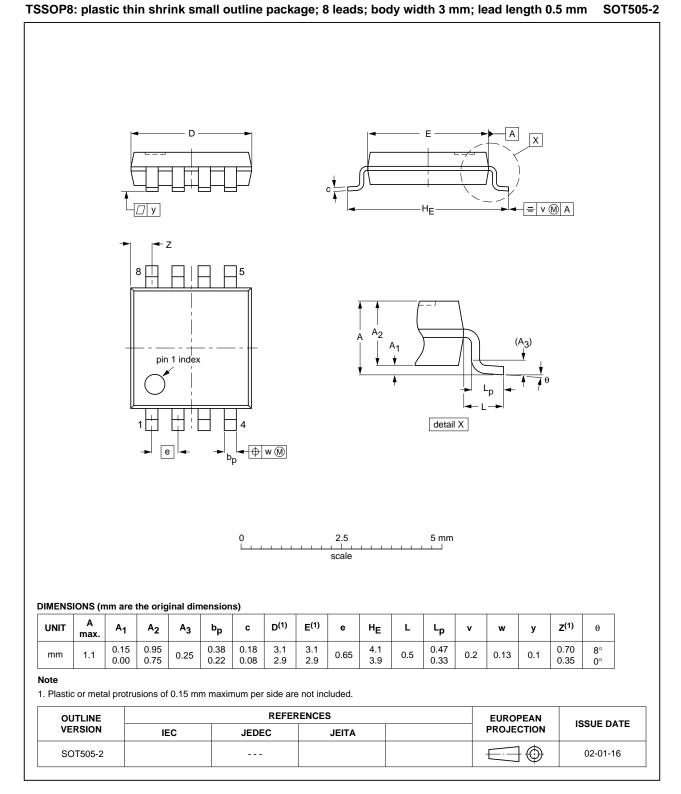


Fig 7. Package outline SOT505-2 (TSSOP8)

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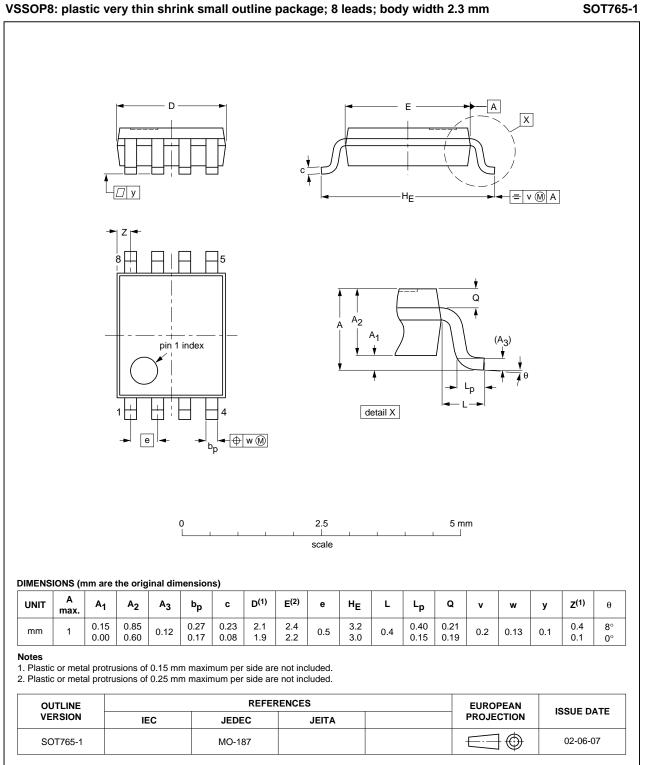
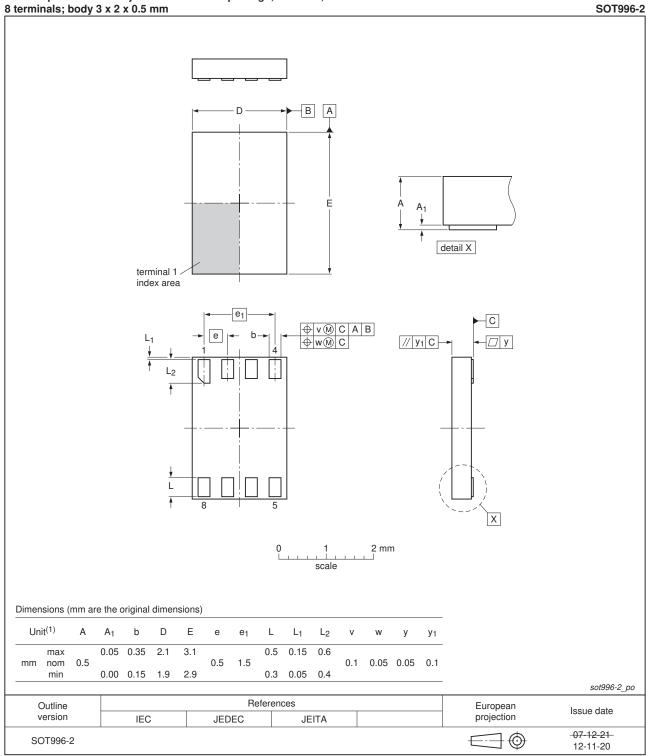


Fig 8. Package outline SOT765-1 (VSSOP8)

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Triple buffer gate



XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

Package outline SOT996-2 (XSON8) Fig 9.

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14. Abbreviations

Table 11. Abbreviations				
Acronym	Description			
CMOS	Complementary Metal Oxide Semiconductor			
DUT	Device Under Test			
ESD	ElectroStatic Discharge			
HBM	Human Body Model			
MM	Machine Model			
TTL	Transistor-Transistor Logic			

15. Revision history

ry			
Release date	Data sheet status	Change notice	Supersedes
20131211	Product data sheet	-	74HC_HCT3G34 v.5
 For type num 	bers 74HC3G34GD and 74HC	T3G34GD XSON8L	J has changed to XSON8.
20090507	Product data sheet	-	74HC_HCT3G34 v.4
20060309	Product data sheet	-	74HC_HCT3G34 v.3
20030519	Product specification	-	74HC_HCT3G34 v.2
20030210	Product specification	-	74HC_HCT3G34 v.1
20031003	Product specification	-	-
	Release date 20131211 • For type num 20090507 20060309 20030519 20030210	Release dateData sheet status20131211Product data sheet• For type numbers 74HC3G34GD and 74HC20090507Product data sheet20060309Product data sheet20030519Product specification20030210Product specification	Release dateData sheet statusChange notice20131211Product data sheet-• For type numbers 74HC3G34GD and 74HCT3G34GD XSON8U20090507Product data sheet20060309Product data sheet20030519Product specification20030210Product specification

16. Legal information

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